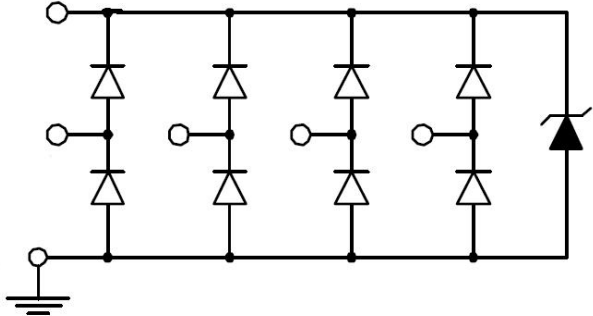
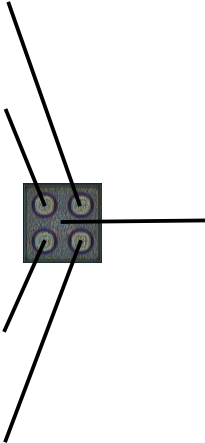



<ul style="list-style-type: none"> 4-Channel Uni-directional ESD diode 	<p>芯片图 WAFER DIAGRAM</p> 
	 <p>产品印记 MARKING</p> <p>PINI</p>

1.0 材料规格 MATERIAL

芯片型号 (Die Type)	LM605ESDP5-0.36	Top metal for wire bond	4 μm AlSiCu
		Gross die per wafer	120,000 dies
		芯片尺寸 (Die Size)	360×360 μm
		晶圆厚度 (Wafer Thickness)	150±10 μm
焊区厚度 (Weld Thickness)		焊区尺寸 (Weld Size)	75×75 μm
焊接方式 (Die Attach Type)		切割道 (Scribe Line)	50 μm
框架型号 (Lead Frame)		芯片厚度 (Wafer thickness)	152±8 μm
焊线规格 (Wire Size)		晶圆直径 (Wafer Diameter)	6 inch
电镀方式 (Plating Method)	---	芯片背材 (BackMetal Material)	TiNiAg

测试规范

Electrical Characteristics (TA=25°C unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V_{RWM}			5	V	
Breakdown Voltage	V_{BR}	7.0	8.0	9.5	V	$I_T=1mA$
Leakage Current	I_{Leak}			100	nA	$V_{RWM}=5V$
正向电压	V_F			1.1	V	$I_F=10mA$

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